

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1336	365/158.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L2	1286	365/171.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L3	856	365/173.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L4	13	oh-hyung-rok.in.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L5	21	cho-woo-yeong.in.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L6	3	kim-su-yeon.in.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:01

Day : Tuesday
Date: 1/31/2006


PALM INTRANET

Time: 13:02:54

Inventor Name Search Result

Your Search was:

Last Name = OH

First Name = HYUNG-ROK

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10660802	6853599	150	09/12/2003	MAGNETIC MEMORY DEVICE IMPLEMENTING READ OPERATION TOLERANT TO BITLINE CLAMP VOLTAGE (VREF)	OH, HYUNG-ROK
10805696	6943395	150	03/22/2004	PHASE RANDOM ACCESS MEMORY WITH HIGH DENSITY	OH, HYUNG-ROK
10828894	Not Issued	80	04/20/2004	Magnetic random access memory device	OH, HYUNG-ROK
10829807	Not Issued	95	04/22/2004	WRITING DRIVER CIRCUIT OF PHASE-CHANGE MEMORY	OH, HYUNG-ROK
10921797	6885602	150	08/20/2004	PROGRAMMING METHOD OF CONTROLLING THE AMOUNT OF WRITE CURRENT APPLIED TO PHASE CHANGE MEMORY DEVICE AND WRITE DRIVER CIRCUIT THEREFOR	OH, HYUNG-ROK
10937943	Not Issued	30	09/11/2004	Phase-change memory device and method that maintains the resistance of a phase-change material in a reset state within a constant resistance range	OH, HYUNG-ROK
10943300	6982913	150	09/17/2004	DATA READ CIRCUIT FOR USE IN A SEMICONDUCTOR MEMORY AND A METHOD THEREOF	OH, HYUNG-ROK
11079198	Not Issued	41	03/15/2005	Programming method of controlling the amount of write current applied to phase change memory device and write driver circuit therefor	OH, HYUNG-ROK
11177115	Not Issued	30	07/08/2005	Phase random access memory with high density	OH, HYUNG-ROK

11220294	Not Issued	30	09/06/2005	Semiconductor memory device capable of compensating for leakage current	OH, HYUNG-ROK
11249858	Not Issued	20	10/13/2005	Data read circuit for use in a semiconductor memory and a method therefor	OH, HYUNG-ROK
11253626	Not Issued	20	10/20/2005	Semiconductor memory device	OH, HYUNG-ROK
11260602	Not Issued	30	10/27/2005	Magneto-resistive RAM having multi-bit cell array structure	OH, HYUNG-ROK

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name	First Name	
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Day : Tuesday
Date: 1/31/2006


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Time: 13:03:39

Inventor Name Search Result

Your Search was:

Last Name = CHO

First Name = WOO-YEONG

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09955458</u>	Not Issued	71	09/18/2001	Reference voltage generating circuit using active resistance device	CHO, WOO-YEONG
<u>10660802</u>	6853599	150	09/12/2003	MAGNETIC MEMORY DEVICE IMPLEMENTING READ OPERATION TOLERANT TO BITLINE CLAMP VOLTAGE (VREF)	CHO, WOO-YEONG
<u>10773901</u>	Not Issued	93	02/06/2004	DEVICE AND METHOD FOR PULSE WIDTH CONTROL IN A PHASE CHANGE MEMORY DEVICE	CHO, WOO-YEONG
<u>10805696</u>	6943395	150	03/22/2004	PHASE RANDOM ACCESS MEMORY WITH HIGH DENSITY	CHO, WOO-YEONG
<u>10828894</u>	Not Issued	80	04/20/2004	Magnetic random access memory device	CHO, WOO-YEONG
<u>10829807</u>	Not Issued	95	04/22/2004	WRITING DRIVER CIRCUIT OF PHASE-CHANGE MEMORY	CHO, WOO-YEONG
<u>10921797</u>	6885602	150	08/20/2004	PROGRAMMING METHOD OF CONTROLLING THE AMOUNT OF WRITE CURRENT APPLIED TO PHASE CHANGE MEMORY DEVICE AND WRITE DRIVER CIRCUIT THEREFOR	CHO, WOO-YEONG
<u>10937943</u>	Not Issued	30	09/11/2004	Phase-change memory device and method that maintains the resistance of a phase-change material in a reset state within a constant resistance range	CHO, WOO-YEONG
<u>10943300</u>	6982913	150	09/17/2004	DATA READ CIRCUIT FOR USE IN A SEMICONDUCTOR MEMORY AND A METHOD THEREOF	CHO, WOO-YEONG

<u>10976626</u>	Not Issued	41	10/29/2004	Nonvolatile semiconductor memory device with scalable two transistor memory cells	CHO, WOO-YEONG
<u>11074557</u>	Not Issued	30	03/08/2005	Phase change memories and/or methods of programming phase change memories using sequential reset control	CHO, WOO-YEONG
<u>11079198</u>	Not Issued	41	03/15/2005	Programming method of controlling the amount of write current applied to phase change memory device and write driver circuit therefor	CHO, WOO-YEONG
<u>11092456</u>	Not Issued	30	03/29/2005	Phase-change memory element driver circuits using measurement to control current and methods of controlling drive current of phase-change memory elements using measurement	CHO, WOO-YEONG
<u>11124341</u>	Not Issued	20	05/06/2005	Control of set/reset pulse in response to peripheral temperature in PRAM device	CHO, WOO-YEONG
<u>11177115</u>	Not Issued	30	07/08/2005	Phase random access memory with high density	CHO, WOO-YEONG
<u>11184184</u>	Not Issued	25	07/19/2005	Phase change memory device for use in a burst read operation and a data reading method thereof	CHO, WOO-YEONG
<u>11249858</u>	Not Issued	20	10/13/2005	Data read circuit for use in a semiconductor memory and a method therefor	CHO, WOO-YEONG
<u>11260602</u>	Not Issued	30	10/27/2005	Magneto-resistive RAM having multi-bit cell array structure	CHO, WOO-YEONG
<u>11303910</u>	Not Issued	20	12/19/2005	Phase change memory device and method of driving word line thereof	CHO, WOO-YEONG
<u>11316256</u>	Not Issued	20	12/23/2005	Phase change random access memory device having variable drive voltage circuit	CHO, WOO-YEONG

Inventor Search Completed: No Records to Display.

Search Another: Inventor

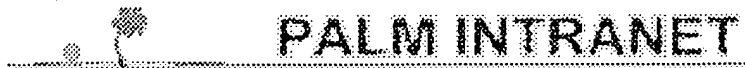
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Date: 1/31/2006

Time: 13:04:01



Inventor Name Search Result

Your Search was:

Last Name = KIM

First Name = SU-YEON

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10660802	6853599	150	09/12/2003	MAGNETIC MEMORY DEVICE IMPLEMENTING READ OPERATION TOLERANT TO BITLINE CLAMP VOLTAGE (VREF)	KIM, SU-YEON
10828894	Not Issued	80	04/20/2004	Magnetic random access memory device	KIM, SU-YEON

Inventor Search Completed: No Records to Display.

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Last Name	First Name	
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